

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Constantin Bulucea

Assignee: National Semiconductor Corporation

Title: Gate-Enhanced Junction Varactor

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AMENDMENT

Sir:

Responsive to the Office Action mailed 28 August 2002, please amend the above patent application as follows. A one-month extension of time accompanies this Response, allowing the Applicants until 28 December 2002 to respond.

IN THE CLAIMS

Amend Claims 20, 23, 29, 31, 32, 38, 43, 44, and 50 to read:

--20. (Amended) A structure as in Claim 19 wherein the plate region occupies a lateral plate area along the primary surface, the varactor has a minimum capacitance dependent on the plate area, an inversion layer that meets the plate region selectively appears and disappears in the body region below the gate electrode.

B1